

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	4550	polysilicon with emitter	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	3	1 same vacancies	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	0	("2006/0097352").URPN.	USPAT
4	BRS	L4	49	polysilicon with vacancies	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	12096	polysilicon with (carbon or c)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	1169	5 and (bipolar adj transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	147	polysilicon with (carbon or c) and vacancies	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	9	polysilicon with ((carbon or c) and vacancies)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	1	polysilicon with ((argon or Ar) and vacancies)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB